

SANYO	No.3234	2SC4480
NPN Epitaxial Planar Silicon Transistor		
Low-Frequency General-Purpose Amp, General Driver Applications		

Features

- Large current capacity
- Adoption of MBIT process
- High DC current gain
- Low collector-to-emitter saturation voltage
- High V_{EBO}

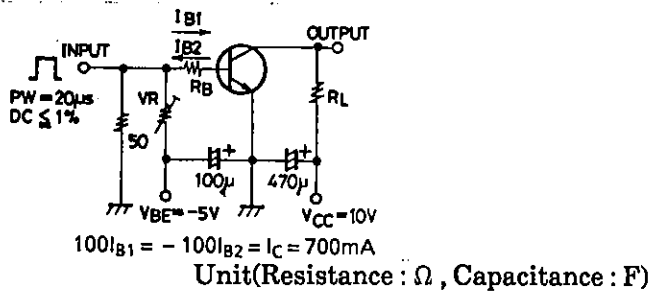
Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

Collector to Base Voltage	V_{CBO}	30	V	
Collector to Emitter Voltage	V_{CEO}	25	V	
Emitter to Base Voltage	V_{EBO}	15	V	
Collector Current	I_C	2	A	
Collector Current(Pulse)	I_{CP}	4	A	
Base Current	I_B	0.4	A	
Collector Dissipation	P_C	1	W	
Junction Temperature	T_j	150	$^\circ\text{C}$	
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$	

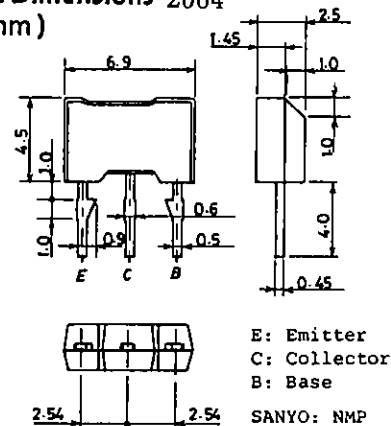
Electrical Characteristics at $T_a = 25^\circ\text{C}$

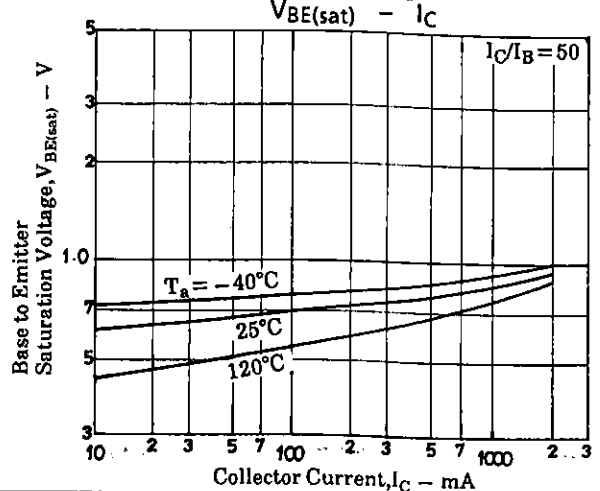
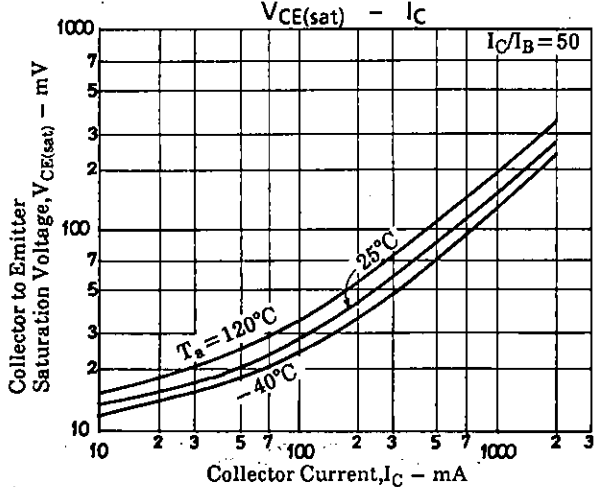
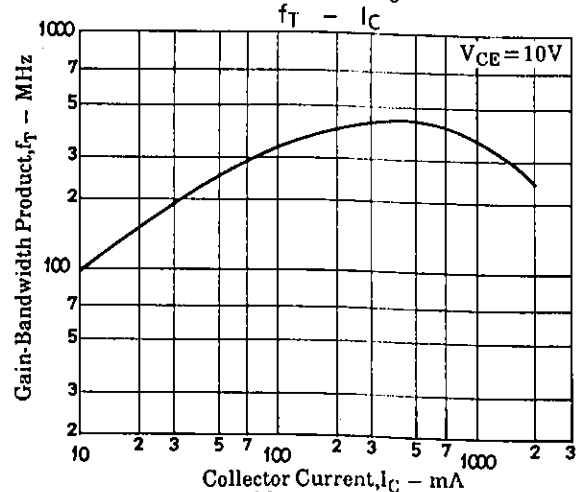
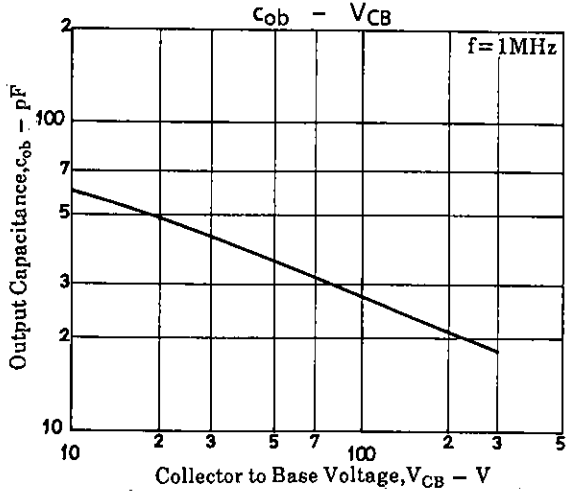
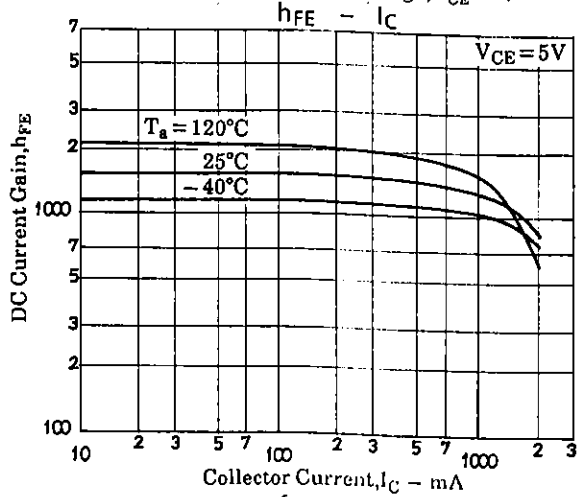
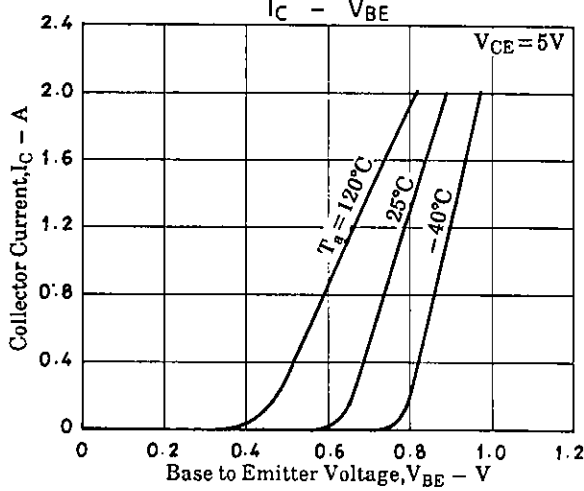
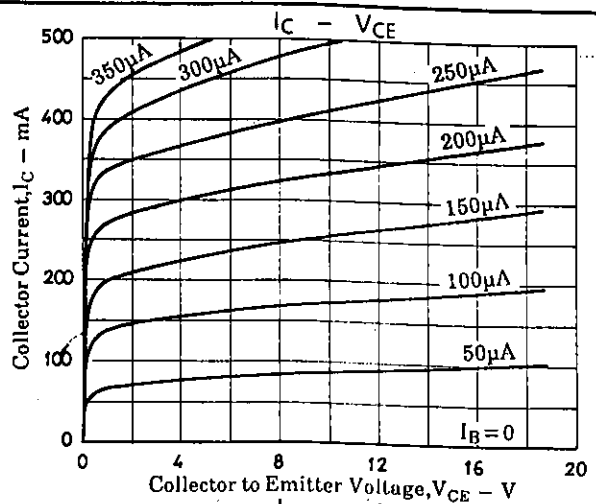
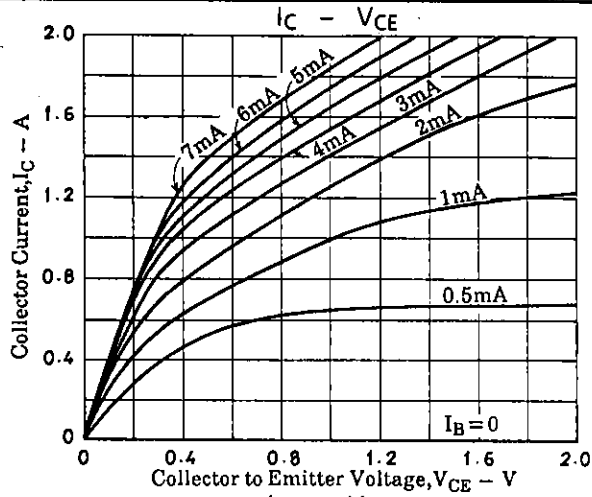
			min	typ	max	
Collector Cutoff Current	I_{CBO} $V_{CB} = 20V, I_E = 0$				100	nA
Emitter Cutoff Current	I_{EBO} $V_{EB} = 10V, I_C = 0$				100	nA
DC Current Gain	$h_{FE}(1)$ $V_{CE} = 5V, I_C = 500mA$	800	1500	3200		
	$h_{FE}(2)$ $V_{CE} = 5V, I_C = 1A$	600				
Gain-Bandwidth Product	f_T $V_{CE} = 10V, I_C = 50mA$		260			MHz
Output Capacitance	c_{ob} $V_{CB} = 10V, f = 1MHz$		27			pF
C-E Saturation Voltage	$V_{CE(sat)}$ $I_C = 1A, I_B = 20mA$	0.15		0.5		V
B-E Saturation Voltage	$V_{BE(sat)}$ $I_C = 1A, I_B = 20mA$	0.85		1.2		V
C-B Breakdown Voltage	$V_{(BR)CBO}$ $I_C = 10\mu A, I_E = 0$	30				V
C-E Breakdown Voltage	$V_{(BR)CEO}$ $I_C = 1mA, R_{BE} = \infty$	25				V
E-B Breakdown Voltage	$V_{(BR)EBO}$ $I_E = 10\mu A, I_C = 0$	15				V
Turn-ON Time	t_{on} See specified Test Circuit.		0.14			μs
Storage Time	t_{stg} "		1.35			μs
Fall Time	t_f "		0.1			μs

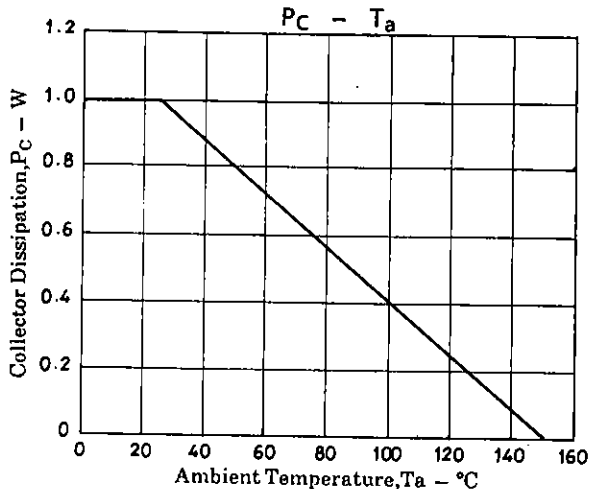
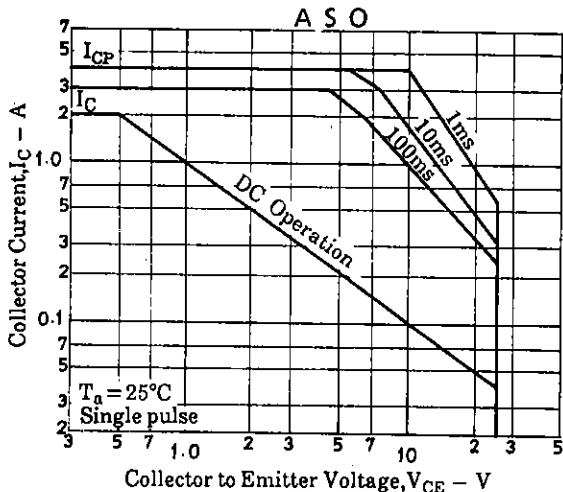
Switching Time Test Circuit



Package Dimensions 2064 (unit: mm)







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